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Scaling of the Coercive Field with Thickness in Thin-Film Ferroelectrics

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Abstract

Motivated by the observed thickness-scaling of the coercive field in ferroelectric films over five decades, we develop a statistical approach towards understanding the conceptual underpinnings of this behavior. Here the scaling exponent is determined by the field-dependence of a known and measured quantity, the nucleation rate per unit area. We end with a discussion of our initial assumptions and point to instances where they could no longer be applicable.

Experimentally the coercive field (E_c) of a thin-film ferroelectric increases with decreasing sample thickness (d).[1,2] Recently we have shown that E_c displays a specific thickness-dependence, $E_c \sim d^{-2/3}$, over five decades ranging from 100 microns down to 1 nanometer.[3] Here we study the conceptual underpinnings of this dramatic scaling behavior. Guided by a set of experimental facts, we develop a statistical approach that yields the expression, $E_c \sim d^{-\frac{1}{\alpha}}$. In particular we find that this exponent α is determined by the field-dependence of another measured quantity, the nucleation rate unit area ($N(E)$). Experimentally it is known[1,4,5] that $\alpha = 3/2$, which then leads to the observed scaling relation, $E_c \sim d^{-2/3}$. Finally we emphasize the necessary conditions for this scaling to occur, indicating situations where it may not be applicable.

The thickness-dependence of the coercive field in ferroelectric films ranging from 100 microns to 200 nanometers has been known to display the relation $E_c \sim d^{-2/3}$ for some time.[2] However recent measurements of E_c for PVDF films down to one nanometer indicate significant deviation from the expected scaling behavior.[6,7] Elsewhere we have noted that at such small length-scales the imperfect conducting nature of the capacitor electrodes becomes important.[3] More specifically the full charge on each plate does not reside in the plane of the ferroelectric-electrode interface, completely compensating for the spontaneous polarization in the ferroelectric film. Rather it is distributed over a small but finite region in the electrode, and there is *incomplete* charge conpensation at the interface. Physically this results in a depolarization field in the film which must play a role in the switching process. Since the potential in the imperfect but realistic electrodes results from the induced charge density it will be proportional to the spontaneous polarization P_s in the film. In many ferroelectric materials P_s is weakly d-dependent so that the depolarization field will scale roughly inversely with d; then the associated corrections will be important in films of decreasing thickness.

The presence of a depolarization potential indicates that the switching field measured by the external circuit is *not* the same as that in the ferroelectric. More specifically the coercive field in the film is[3]

$$E_c = \frac{V + 8\pi P_s a}{d + \epsilon_f(2a)} \tag{1}$$

where V is the voltage drop across the capacitor, $a = \frac{\lambda}{\epsilon_e}$ is a normalized screening length (λ) associated with the charge, and ϵ_e and ϵ_f are the dielectric constants of the metal electrodes and the film respectively. Here we have assumed a Yukawa form for the charge density at the ferrolectric-electrode interface. We observe that when $a = 0$ we recover the result that the film and the measured fields are identical ($E_c = \frac{V}{d}$). For PVDF the addition of such depolarization corrections to the measured coercive fields leads to the recovery of the scaling behavior. We refer the interested reader elsewhere for more details of this treatment.[3] In Figure 1 we present a normalized scaling plot of $\log \frac{E_c}{C}$ vs $\log d$ where C for three distinct material types of ferroelectric films and note that the slope of this line is $s = -0.66$ for five decades; here C is a materials-specific thickness-independent normalization constant. For the PVDF data, we estimated the screening length associated with the aluminum electrodes to be $a = 0.45\mathring{A}$ using a Thomas-Fermi approximation;[3] in the inset of Figure 1 we display the inverse capacitance vs. thickness data for the PVDF films,[6,7] and note that our fit yields $a = 0.34 \pm 0.15\mathring{A}$ so that our estimate is within the bounds set by the experiment.

Motivated by the tremendous success of this semi-empirical scaling relation, $E_c \sim d^{-2/3}$, we now turn towards understanding its conceptual foundations. First, we recall that an electric field is proportional to a force and thus is usually an intensive quantity. Thus the observation that the coercive field is thickness-dependent indicates the breakdown of standard self-averaging. This raises the possibility that homogenous nucleation might be responsible for the observed $E_c(d)$, since here rare fluctuations determine physical quantities. However such processes have been shown to be energetically improbable in ferroelectrics.[8] Furthermore we expect that the probability of having rare fluctuations anywhere in the sample would increase with system size, resulting in a decreasing E_c with diminishing thickness in contradiction with observation.

We can posit a voltage drop across a surface layer at the metal-ferroelectric interface; then the coercive field of the entire ferroelectric film is thickness-dependent. However the

resulting E_c is inversely proportional to d, which is not in agreement with experiment.[1] Noting the observed scaling behavior, $E_c \sim d^{-2/3}$, Janovec[9] and later Kay and Dunn[10] developed phenomenological appproaches to the problem that involved the characterization of rare fluctuations at the metal-electrode boundary. Though conceptually appealing, their treatments were logically inconsistent since they applied ideas of homogenous nucleation, with uniform probability of reverse-domain creation throughout the film, to particular sites on the sample boundary. The observed d-dependence of E_c is recovered in these papers, and results from the specific geometry of the critical nucleus, a half prolate spheroid.[9,10] This conceptual pathway to the scaling law is somewhat surprising given the latter's broad application to materials with rather different microscopic qualities. Finally it is important to establish the working limits of this scaling behavior; for example, clearly it will not be appropriate for bulk crystals.

The coercive field is a kinetic quantity, and the associated switching involves many complex processes that include the nucleation and growth of a distribution of domains. Clearly any theoretical attempt to recover the observed scaling behavior must be guided by experiment in its choice of initial assumptions. Here we use a statistical approach to model E_c, restricting our attention to its quasi-static amplitude. Supported by imaging measurements,[11–13] we argue that the nucleation of "dissident" domains in thin ferroelectric films is most probable at the electrode boundaries. The reversal of the sample's macroscopic polarization is initiated by the nucleation and subsequent growth of many of these independent domains that develop in parallel (cf. Figure 2). This approach clearly neglects long-range interactions in the system, though it can be adapted to include them at the mean-field level.[14,15] However we expect that in thin films, the Coulomb force will be screened by charges on the ferroelectric-electrode interfaces. Elastic interactions can have important scale-dependent effects on the transition temperatures in these systems,[16] but they are not expected to contribute to $E_c(d)$ since the strain energy is usually weakly dependent on field direction.

We now show that the observed thickness scaling of the coercive field can be recovered

from an adapted Kolmogorov-Avrami model[17] of *inhomogenous* nucleation in a confined geometry. The coercive field is defined by the condition that half the sample is transformed. More specifically the thickness-dependence of E_c is determined by the expression $U(E,d)|_{E=E_c} = \frac{1}{2}$ where $U(E,d)$ is the untransformed sample fraction as a function of applied (quasi-static) field E and thickness d. In a model of nucleation and growth, the rate of transformation of a region at time t is governed not only by the nucleation rate there but also by the probability that a domain that was nucleated earlier somewhere else in the sample sweeps into the region in question. As mentioned above, there is strong evidence from experiment[2,11,12] that nucleation events occur predominantly at the ferroelectric-electrode interface. For the large electric fields ($\geq$ 10 kV/cm) corresponding to the thin-films of our study, it is known that v_f, the forward domain velocity, is of the order of the speed of sound.[1] By contrast v_l, the lateral domain motion is field-dependent and is significantly slower;[1] furthermore it is not expected have a strong dependence on film thickness[1] and should therefore make a neglible contribution to $E_c(d)$. In our treatment we will therefore assume that the nucleation rate, known to increase with increasing field strength,[1] is high enough that the film is transformed by large numbers of independent nucleation events, rather than by the slow lateral growth of a few domains (cf. Figure 2); this approximation is supported by a detailed quantitative analysis[18] for PZT films of dimensions comparable to those used in this study.

The rate of change of the untransformed fraction of the sample, $U(E,d)$, decreases as a function of increasing time, and is proportional to the product of the material available, $U(E,d)$, and the nucleation rate. For the homogenous case, where nucleation is equally probable throughout the sample, this rate is defined as the nucleation per unit volume multiplied by a characteristic volume that the critical nucleus has swept out in a given time. By contrast for the interface-specific inhomogenous nucleation considered here, we are interested in a nucleation rate per unit area, N, and the lateral area of a domain, $\mathcal{A}$; experimentally $N = N(E)$ is known to be field-dependent.[1] We therefore obtain a simple expression for the time-dependence of $U(E,d)$

$$\frac{dU}{dt} \approx -UN(E)\mathcal{A} \tag{2}$$

where we implicity assume that the time associated with the domain to propagate across the thickness of the film, t_f, is shorter than the period of the a.c. driving electric field. This time-scale, $t_f = \frac{d}{v_f}$, is roughly a nanosecond for a micron-thick film[2] where the forward domain velocity, v_f, is of order the speed of sound and is known to be asymptotically independent of field-strength at high fields;[1,19] we note that the thickness provides a natural time-scale that cuts off the time evolution of the system. The resulting expression for the fraction of the sample untransformed as function of field and thickness, can therefore be taken to be quasi-static for all practical measurements since domain propagation across the film is effectively instantaneous[1,2]. With the time replaced by the natural time scale t_f, we have

$$U(E,d) \sim \exp -N(E)\left(\frac{\mathcal{A}d}{v_f}\right). \tag{3}$$

It is important to note that within this framework many independent nucleation and growth events occur in parallel, so that the detailed nature of the final state is not crucial (cf. Figure 2). In Figure 2 we assume columnar grains for graphical simplicity;[20] there the shaded regions refer to the untranformed parts of the sample.

The equation (3) is valid with the implicit underlying assumption that nucleation dominates over lateral growth. In order to obtain a more quantitative condition for the validity of this expression, we can do a direct comparision of these two different rates. More specifically, the change in time of the transformed fraction by lateral growth is proportional to the number of transformed domains ($\frac{1-U}{\mathcal{A}}$) and their lateral velocity ($\frac{d\mathcal{A}}{dt}$) which results in

$$\frac{d(1-U)}{dt} = (1-U)\frac{d\ln\mathcal{A}}{dt}. \tag{4}$$

An expression for a similar change due to nucleation is simply proportional to the untransformed fraction and the nucleation rate and is

$$\frac{d(1-U)}{dt} = UN\mathcal{A}. \tag{5}$$

Then in order for lateral growth to be less important than nucleation we must have

$$\frac{d \ln \mathcal{A}}{dt} << N\mathcal{A} \tag{6}$$

where we take $U \sim \frac{1}{2}$ since this is its value when $E \sim E_C$. Therefore (6) is our working premise for the validity of equation (3) and all that follows from it. We note that recent atomic force microscopy studies of switching in thin ferroelectric films support our contention that it is dominated by domain forward growth processes.[21]

For field-strengths greater than $10kV/cm$, relevant for the thin-films studied here, the nucleation rate per unit area is known to have a power-law dependence on applied field.[1] If we accordingly put $N(E) \sim E^{\alpha}$ in (3), the expression for the thickness-dependence of the coercive field, $U(E_c, d) = \frac{1}{2}$, becomes $E_c^{\alpha} d \sim 1$; this then yields

$$E_c \sim d^{-\frac{1}{\alpha}}. \tag{7}$$

Experimentally[4] and theoretically,[5] it is known from switching kinetics that $\alpha = \frac{3}{2}$ over a broad range of fields; this value of α then leads to the result $E_c \sim d^{-2/3}$. We note that the scaling of E_c with thickness follows directly from the field-dependence of the density of nucleation sites, $N(E)$, which is a *statistical* quantity that could plausibly have similar behavior for materials with different microscopic features.

We have therefore successfully recovered the observed thickness scaling of the coercive field using a statistical approach that is not dependent on particular sample specifics. It is important to be clear about our underlying assumptions, and to point to situations where they could break down. First of all, we have assumed that nucleation of new reverse-polarization domains occur solely at the ferroelectric-electrode interface. Next we have considered situations where the transformation of the new polarization domains occurs predominantly by nucleation and *not* by lateral growth of preexisting "dissident" ones. Finally we assume that, once formed, the new domains grow unimpeded to the other side of the film. Clearly these assumptions will not be valid for all ferroelectric capacitors. For example it is known[18] that for thicker samples than those considered here, the switching process is dominated by lateral growth. The specific length-scale where this occurs depends on material-specific quantities.[18]

Similarly in disordered and granular films, grain boundaries and charge vacancies could act as nucleation centers away from the sample edges.[13] Finally defects in the ferroelectric could obstruct the motion of domains, and then again we would not expect the scaling relation discussed here to be appropriate.

In summary, we have presented a statistical model that leads to a specific thickness-dependence of the coercive field. This scaling behavior is observed over five decades of length-scale in several different materials.[3] Guided by a number of experimental observations, we recover the observed scaling by assuming that nucleation at the electrode interface dominates the switching process, and that the resulting "dissident" domains propagate uninhibited across the film's thickness. The exponent associated with the functional form of $E_c(d)$ is related to another known and measured exponent, that associated with the field-dependence of the nucleation rate per unit area. We emphasize that $N(E)$ is a quantity that is not dependent on sample microscopics, and thus our result is compatible with experimental findings. We note that there remain a number of unresolved theoretical issues associated with this derivation of E_c that include the calculation of realistic energy barriers and the determination of the absolute rather than the relative magnitude of E_c. Finally we would like to study the behavior of the coercive field at finite-frequency, and in this case it may not be possible to neglect the long-range elastic and Coulomb interactions as we have done here.

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Figure Captions

Fig. 1. **(Main Figure)** The normalized corrected log coercive field vs. log thickness which indicates scaling over five decades of length-scale. The slope is -0.66 ± 0.02, in agreement with the theoretical value of $-\frac{2}{3}$. **(Inset)** Inverse-capacitance vs. thickness of PVDF data[6] where the y-intercept is related to the screening length used in the depolarization correction.

Fig. 2. A schematic of the statistical approach to the scaling law. The sample is originally poled (a). Application of a small electric field leads to a number of nucleation events at the electrodes, $N(E)$, which then grow across the same. For $E < E_c$, the fraction of the sample that is untransformed (shaded regions), $U(E)$, is more than one-half. The nucleation density of reverse-polarization domains increases with increasing applied field, $N(E) \sim E^{\alpha}$. For $E = E_c$, one-half of the system remains untransformed. Details of the domain structure of the final state are not important, and the thickness-dependence of E_c is determined by the field-dependence of the nucleation density.

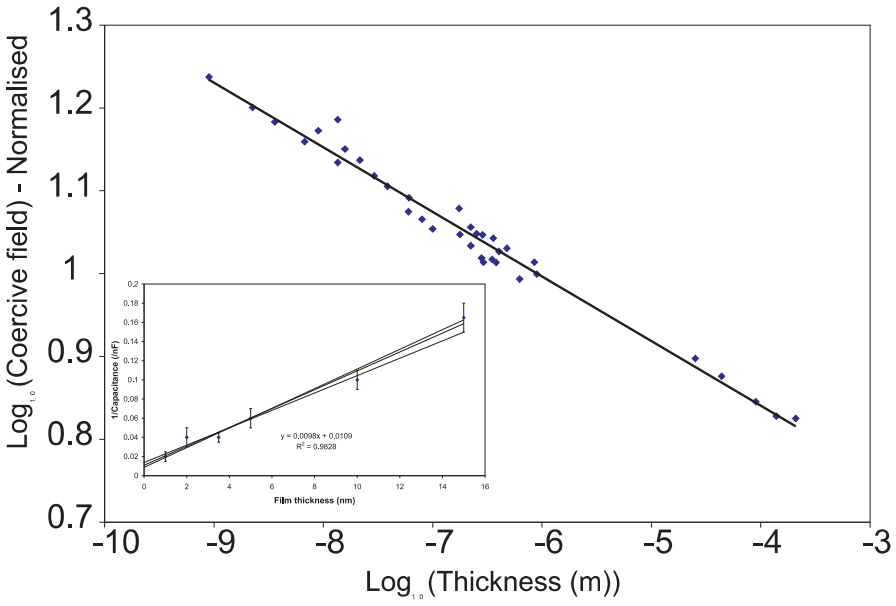

Log10 (Coercive field) - Normalised
Log10 (Thickness (m))
1.3
1.2
1.1
1
0.9
0.8
0.7
-10
-9
-8
-7
-6
-5
-4
-3
1/Capacitance (nF)
Film thickness (nm)
y = 0,0098x + 0,0109
R2 = 0,9828

Fig. 1

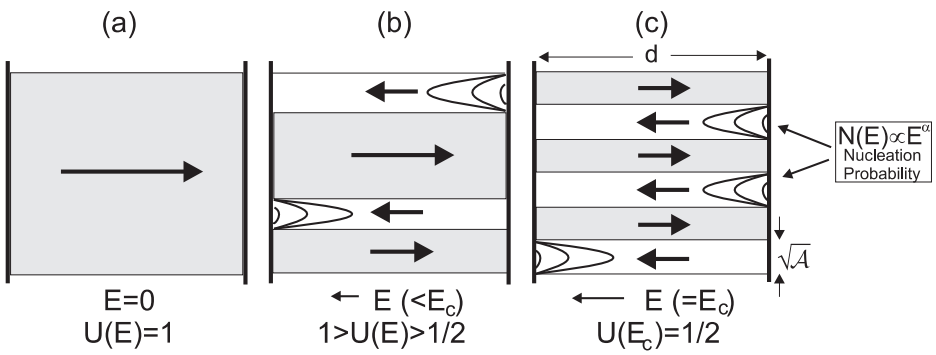

(a)
(b)
(c)
d
N(E)∝E^α
Nucleation
Probability
√A
E=0
U(E)=1
← E (<Ec)
1>U(E)>1/2
← E (=Ec)
U(Ec)=1/2

Fig. 2